

*SPECIFICATION AMENDMENTS*

Replace paragraph [0028] with:

Nine polishing systems (A – I) were prepared, each of which contained about 0.6 wt.% fumed silica (Cabot's Cab-O-Sil® L-90 fumed silica), about 0.25 wt.% gamma-ureidopropyltrimethoxysilane, about 0.04 wt.% benzotriazole, about 0.03 wt.% potassium hydroxide, about 0.004 wt.% potassium carbonate, water, and either no polishing additive (polishing system A) or 1 wt.% of a polishing additive (polishing systems B – I). The polishing additive was different in each polishing system and was either tartaric acid (polishing system B), N-acetyl glycine (polishing system C), potassium oxalate (polishing system D), aminotri(methylenephosphonic acid) (polishing system E), ammonium sulfate (polishing system F), ammonium acetate (polishing system G), diammonium EDTA (polishing system H), or ammonium oxalate (polishing system I). Thus, this example involved a control polishing system (A), comparative polishing systems ~~(B–I)~~ (B – H), and the polishing system of the invention (I). Each of these polishing systems was used to polish a similar semiconductor wafer comprising copper, tantalum, and TEOS under similar conditions. The rate at which the copper on the substrate was removed was determined for each polishing system.